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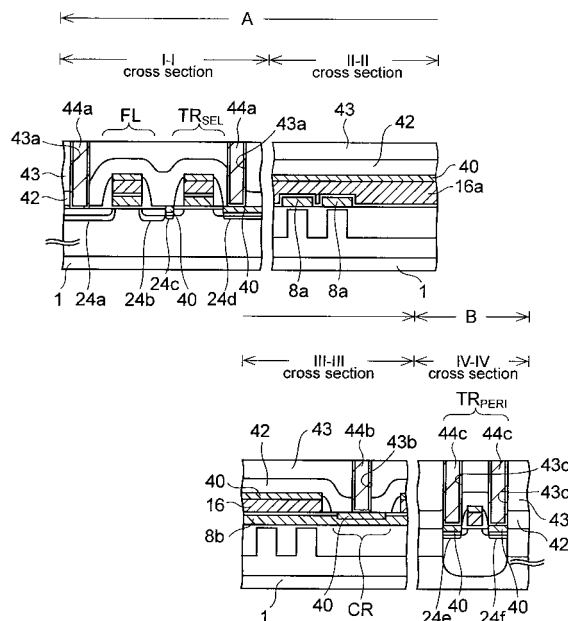
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(54) **Semiconductor device and method for manufacturing the same**

(57) A method for manufacturing a semiconductor device including the steps of forming a flash memory cell (FL) provided with a floating gate (8a), an intermediate insulating film (12), and a control gate (16a), forming first and second impurity diffusion regions (24a, 24b), thermally oxidizing surfaces of a silicon substrate (1) and the floating gate (8a), etching a tunnel insulating film in a partial region (PR) through a window (39b) of a resist pattern (39); forming a metal silicide layer (40) on the first impurity diffusion region (24a) in the partial region (PR), forming an interlayer insulating film (43) covering the flash memory cell (FL), and forming, in a first hole (43a) of the interlayer insulating film (43), a conductive plug (44) connected to the metal silicide layer (40).

FIG. 1T





EUROPEAN SEARCH REPORT

Application Number
EP 08 10 0340

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The present search report has been drawn up for all claims			
Place of search The Hague		Date of completion of the search 19 March 2009	Examiner Rosello Garcia, M
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2
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**ANNEX TO THE EUROPEAN SEARCH REPORT
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